INCH-POUND

MIL-M-38510/319C 14 July 2003 SUPERSEDING MIL-M-38510/319B 4 March 1985

MILITARY SPECIFICATION

MICROCIRCUITS, DIGITAL, LOW-POWER SCHOTTKY TTL, 4 BY 4 REGISTER FILE, CASCADABLE, MONOLITHIC SILICON

Inactive for new design after 18 April 1997.

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 <u>Scope.</u> This specification covers the detail requirements for monolithic silicon, Schottky TTL, low-power, 4 by 4 register file microcircuits. Two product assurance classes and a choice of case outlines and lead finishes are provided for each type and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.3).

1.2 Part number. The part number should be in accordance with MIL-PRF-38535, and as specified herein.

1.2.1 <u>Device types.</u> The device types should be as follows:

Device type	Circuit
01	4 by 4 register file with 3-state outputs, cascadable
02	4 by 4 register file with open collector outputs, cascadable

1.2.2 Device class. The device class should be the product assurance level as defined in MIL-PRF-38535.

1.2.3 Case outlines. The case outlines should be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
Е	GDIP1-T16 or CDIP2-T16	16	Dual-in-line
F	GDFP2-F16 or CDFP3-F16	16	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAS, P. O. Box 3990, Columbus, OH 43216-5000, by using the self addressed Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

AMSC N/A <u>DISTRIBUTION STATEMENT A.</u> Approved for public release; distribution is unlimited. FSC 5962

1.3 Absolute maximum ratings.

Supply voltage range Input voltage range	
Storage temperature range	
Maximum power dissipation (P _D) <u>1</u> /	
Device type 01	. 275 mW
Device type 02	. 220 mW
Lead temperature (soldering, 10 seconds)	. 300°C
Thermal resistance, junction to case (θ_{JC}) :	
Cases E, F, and 2	. (See MIL-STD-1835)
Junction temperature (T _J) <u>2</u> /	. +175°C

1.4 Recommended operating conditions.

Supply voltage (V _{CC})	
Minimum high level input voltage (V _{IH})	2.0 V
Maximum low level input voltage (VIL)	0.7 V
Case operating temperature range (T _c)	-55°C to +125°C
Minimum width of write enable or read enable pulse	25 ns
Minimum setup time (data)	10 ns
Minimum setup time (write select)	15 ns
Minimum hold time (data)	15 ns (with respect to GW)
Minimum hold time (write select)	5 ns
Minimum latch time for new data	

2. APPLICABLE DOCUMENTS

2.1 Government documents.

2.1.1 <u>Specifications and Standards.</u> The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents shall be those listed in the issue of the Departments of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883	-	Test Method Standard for Microelectronics.
MIL-STD-1835	-	Interface Standard Electronic Component Case Outlines

(Unless otherwise indicated, copies of the above specifications and standards are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence.</u> In the event of a conflict between the text of this specification and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

 $[\]underline{1}$ Must withstand the added P_D due to short-circuit test (e.g., I_{OS}).

^{2/} Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions in accordance with MIL-PRF-38535.

3. REQUIREMENTS

3.1 <u>Qualification</u>. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).

3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.3 <u>Design, construction, and physical dimensions.</u> The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.

3.3.1 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.

3.3.2 Truth table. The truth table shall be as specified on figure 2.

3.3.3 Logic diagram. The logic diagram shall be as specified on figure 3.

3.3.4 <u>Schematic circuits</u>. The schematic circuits shall be_maintained by the manufacturer and made available to the qualifying activity and the preparing activity upon request.

3.3.5 Case outlines. The case outlines shall be as specified in 1.2.3.

3.4 Lead material and finish. The lead material and finish shall be in accordance with MIL-PRF-38535 (see 6.6).

3.5 <u>Electrical performance characteristics</u>. The electrical performance characteristics are as specified in table I, and apply over the full recommended case operating temperature range, unless otherwise specified.

3.6 <u>Electrical test requirements</u>. The electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.

3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.

3.8 <u>Microcircuit group assignment</u>. The devices covered by this specification shall be in microcircuit group number 12 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.

4.2 <u>Screening</u>. Screening shall be in accordance with, MIL-PRF-38535 and shall be conducted on all devices prior to qualification and quality conformance inspection. The following additional criteria shall apply:

- a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
- c. Additional screening for space level product shall be as specified in MIL-PRF-38535, appendix B.

Test	Symbol	Conditions	ns Device		Limits		
		$-55^{\circ}C \le T_{C} \le +125^{\circ}C$	type	Min	Max		
High level output voltage	V _{OH}	$V_{CC} = 4.5 \text{ V}, V_{IN} = 2.0 \text{ V}$ $I_{OH} = -1 \text{ mA}$	01	2.4		V	
Collector cutoff current	I _{CEX}	$V_{CC} = 4.5 \text{ V}, V_{OH} = 5.5 \text{ V}$	02		20	μΑ	
Low level output voltage	V _{OL}	$V_{CC} = 4.5 \text{ V}, \text{ V}_{IN} = 0.7 \text{ V}$ $I_{OL} = 4 \text{ mA}$	01, 02		0.4	V	
Input clamp voltage	V _{IC}	$V_{CC} = 4.5 \text{ V}, \text{ I}_{\text{IN}} = -18 \text{ mA},$ $T_{C} = +25^{\circ}\text{C}$	01, 02		-1.5	V	
High level input current all inputs except GR and GW	I _{IH1}	$V_{CC} = 5.5 \text{ V}, V_{IN} = 2.7 \text{ V}$	01, 02		20	μA	
High level input current	I _{IH2}	$V_{CC} = 5.5 \text{ V}, V_{IN} = 2.7 \text{ V}$	01		60	μA	
at GR			02		40		
High level input current at GW	I _{IH3}	$V_{CC} = 5.5 \text{ V}, V_{IN} = 2.7 \text{ V}$	01, 02		40	μA	
High level input current all inputs except GR and GW	I _{IH4}	$V_{CC} = 5.5 \text{ V}, V_{IN} = 5.5 \text{ V}$	01, 02		100	μA	
High level input current	I _{IH5}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 5.5 \text{ V}$	01		300	μA	
at GR			02		200		
High level input current at GW	I _{IH6}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 5.5 \text{ V}$	01, 02		200	μA	
Off state output current, high level voltage applied	I _{OZH}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{O} = 2.7 \text{ V}$	01		20	μA	
Off state output current: low level voltage applied	I _{OZL}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{O} = 0.4 \text{ V}$	01		-20	μA	
Low level input current at data, read select, and write select		$V_{CC} = 5.5 \text{ V}, V_{IN} = 0.4 \text{ V}$	01, 02	-0.5	-460	μA	
Low level input current at	I _{IL2}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 0.4 \text{ V}$	01	-90	-1300	μA	
read enable			02	-90	-900		
Low level input current at write enable	I _{IL3}	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0.4 \text{ V}$	01, 02	-60	-840	μA	
Short circuit output current	los	V _{CC} = 5.5 V <u>1</u> /	01	-15	-130	mA	
Supply current	I _{CC}	V _{CC} = 5.5 V	01		50 40	mA	

TABLE I. Electrical performance characteristics.

See footnote at end of table.

Test	Symbol	Conditions	Device	Lin	nits	Unit
		$-55^{\circ}C \le T_C \le +125^{\circ}C$	type	Min	Max	
Propagation delay time,	t _{PLH1}	$V_{CC} = 5.0 \text{ V}, \text{ C}_{L} = 50 \text{ pF} \pm 10\%,$	01	2	65	ns
low to high level from data		$R_{L} = 316 \Omega \pm 5\%$ for device type 01,	02	2	65	
Propagation delay time,	t _{PLH2}	$R_{L} = 2 \text{ k}\Omega \pm 5\%$ for device type 02	01	2	58	ns
low to high level from read select			02	2	58	
Propagation delay time,	t _{PHL1}		01	2	58	ns
high to low level from data			02	2	52	
Propagation delay time,	t _{PHL2}		01	2	65	ns
low to high level from read select			02	2	58	
Propagation delay time,	t _{PLH3}		01	2	65	ns
low to high level from write enable			02	2	65	
Propagation delay time, low to high level from read enable	t _{PLH4}		02	2	46	ns
Propagation delay time,	t _{PHL3}		01	2	72	ns
high to low level from write enable			02	2	58	
Propagation delay time, high to low level from read enable	t _{PHL4}		02	2	46	ns
Output enable time to low level	t _{PZL}		01	2	58	ns
Output enable time to high level	t _{PZH}		01	2	52	ns
Output disable time to low level	t _{PLZ}		01	2	52	ns
Output disable time to high level	t _{PHZ}		01	2	72	ns

TABLE I. Electrical performance characteristics - Continued.

 $\underline{1}$ Not more than one output should be shorted at one time.

	Subgroups (see table II		
MIL-PRF-38535	Class S	Class B	
test requirements	devices	devices	
Interim electrical parameters	1	1	
Final electrical test parameters	1*, 2, 3, 7, 9, 10, 11	1*, 2, 3, 7, 9	
Group A test requirements	1, 2, 3, 7, 8, 9, 10, 11	1, 2, 3, 7, 8, 9, 10, 11	
Group B electrical test parameters when using method 5005 QCI option	1, 2, 3, 7, 8 9, 10, 11	N/A	
Group C end-point electrical parameters	1, 2, 3, 7, 8 9, 10, 11	1, 2, 3	
Group D end-point electrical parameters	1, 2, 3	1, 2, 3	

TABLE II. Electrical test requirements.

*PDA applies to subgroup 1.

4.3 <u>Qualification inspection</u>. Qualification inspection shall be in accordance with MIL-PRF-38535.

4.4 Technology <u>Conformance Inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection. Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:

- a. Tests shall be as specified in table II herein.
- b. Subgroups 4, 5, and 6 shall be omitted.
- 4.4.2 Group B inspection. Group B inspection shall be in accordance with table II MIL-PRF-38535.

4.4.3 Group C inspection. Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:

- a. End-point electrical parameters shall be as specified in table II herein.
- b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.4 <u>Group D inspection</u>. Group D inspection shall be in accordance with table V of MIL-PRF-38535. End-point electrical parameters shall be as specified in table II herein.

4.5 <u>Methods of inspection</u>. Methods of inspection shall be specified and as follows:

4.5.1 <u>Voltage and current.</u> All voltages given are referenced to the microcircuit ground terminal. Currents given are conventional and positive when flowing into the referenced terminal.

	Pin ider	ntification		
Pin	Device types 01 and 02			
number	Case 2	Case E, F		
1	NC	Data D2		
2	Data D2	Data D3		
3	Data D3	Data D4		
4	Data D4	Read Select RB		
5	Read Select RB	Read Select RA		
6	NC	Output Q4		
7	Read Select RA	Output Q3		
8	Output Q4	GND		
9	Output Q3	Output Q2		
10	GND	Output Q1		
11	NC	Read Enable GR		
12	Output Q2	Write Enable GW		
13	Output Q1	Write Select WB		
14	Read Enable GR	Write Select WA		
15	Write Enable GW	Data D1		
16	NC	Vcc		
17	Write Select WB			
18	Write Select WA			
19	Data D1			
20	V _{CC}			

FIGURE 1. Terminal connections.

Device type 01

Write function table (see notes A, B, and C)

W	rite inpu	its		Wo	rd	
WB	WA	GW	Q	1	2	3
L	L	L	Q = D	Q_0	Q_0	Q_0
L	Н	L	Q_0	Q = D	Q_0	Q_0
Н	L	L	Q_0	Q_0	Q = D	Q_0
Н	Н	L	Q_0	Q_0	Q_0	Q = D
Х	Х	Н	Q_0	Q ₀	Q_0	Q_0

Read function table ((see notes A and D)
-----------------------	---------------------

Read inputs				Out	outs	
RB	RA	GR	Q1	Q2	Q3	Q4
L	L	L	W0B1	W0B2	W0B3	W0B4
L	Н	L	W1B1	W1B2	W1B3	W1B4
Н	L	L	W2B1	W2B2	W2B3	W2B4
Н	Н	L	W3B1	W3B2	W3B3	W3B4
Х	Х	Н	Z	Z	Z	Z

NOTES:

A. H = high level, L = low level, X = irrelevant, Z = high impedance (off)

B. (Q = D) - The four selected internal flip-flop outputs will assume the states applied to the four external data inputs.

C. Q_0 = the level of Q before the indicated input conditions were established.

D. W0B1 = The first bit of word 0, etc.

Device type 02

Write function table (see notes A, B, and C)

W	rite inpu	ts		Wo	rd	
WB	WA	GW	Q	1	2	3
L	L	L	Q = D	Q_0	Q_0	Q ₀
L	Н	L	Q_0	Q = D	Q_0	Q ₀
Н	L	L	Q_0	Q_0	Q = D	Q_0
Н	Н	L	Q_0	Q_0	Q_0	Q = D
Х	Х	Н	Q_0	Q ₀	Q_0	Q ₀

R	ead inpu	ts		Out	puts	
RB	RA	GR	Q1	Q2	Q3	Q4
L	L	L	W0B1	W0B2	W0B3	W0B4
L	Н	L	W1B1	W1B2	W1B3	W1B4
н	L	L	W2B1	W2B2	W2B3	W2B4
Н	Н	L	W3B1	W3B2	W3B3	W3B4
Х	Х	Н	Н	Н	Н	Н

NOTES:

A. H = high level, L = low level, X = irrelevant

B. (Q = D) - The four selected internal flip-flop outputs will assume the states applied to the four external data inputs.

C. Q_0 = the level of Q before the indicated input conditions were established.

D. W0B1 = The first bit of word 0, etc.

FIGURE 2. Truth tables.



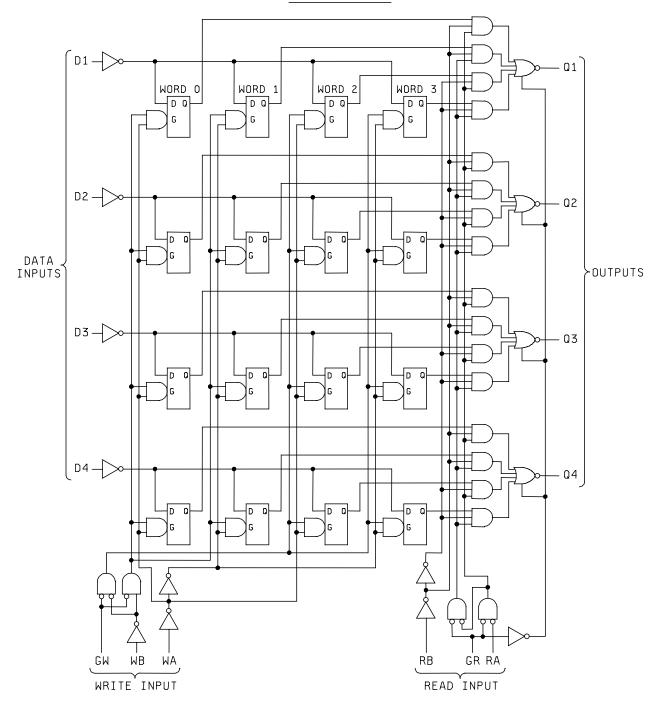


FIGURE 3 Logic diagram.



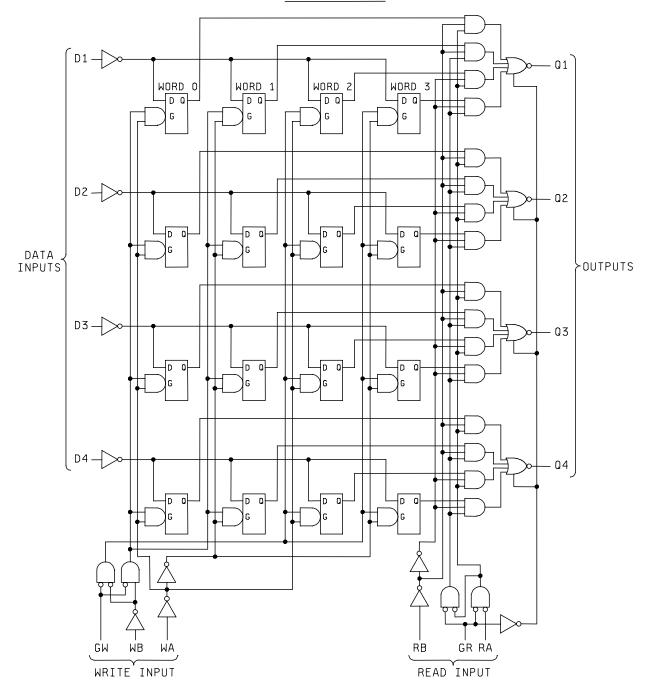
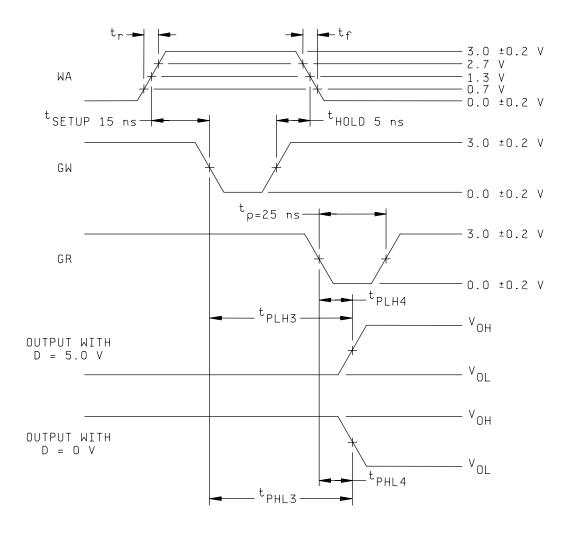


FIGURE 3 Logic diagram - Continued.



NOTES:

- 1. Input pulse characteristics: PRR \leq 1.0 MHz, t_r \leq 15 ns, t_f \leq 6 ns, duty cycle = 50% ±15%.
- 2. $C_L = 50 \text{ pF} \pm 10\%$. C_L includes probe and jig capacitance.
- 3. All diodes are 1N3064 and 1N916.
- 4. Load circuits on a given output are required only where the specific test given in table III indicates "OUT" on that output. Load circuits may otherwise be omitted.

FIGURE 4. Switching test circuit and waveforms for device types 01 and 02.

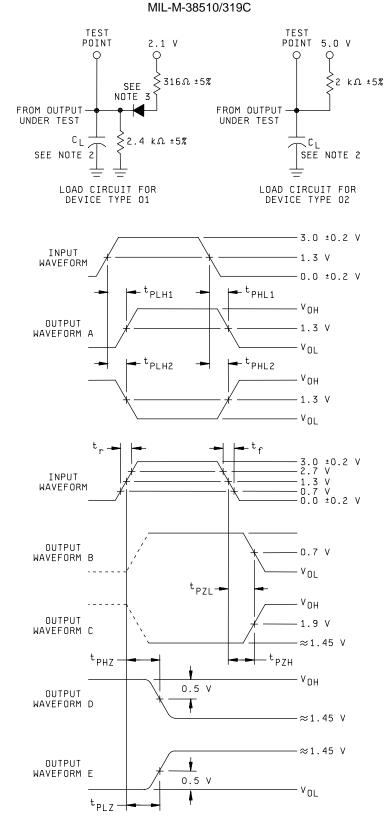


FIGURE 4. Switching test circuit and waveforms for device types 01 and 02 - Continued.

		Unit		>	-	-	-	-	-	-		-	-		-		-	-	-	-	-	Αų	=	-	-	-	-	-	-	-	-	-	-		-	-	-	-	-				-	-	-	=	-		-	-	-
		ş	Мах	0.4	-		-					-1.5	-	=		-		=	=	=	-	1/	=		-		-	-	=	-	-	20	-		=	=	=	-	-	09	40	100	-	=	=	=	-	-		300	200
		Limits	Min					2.4	=	=	-											1/																													
		Measured terminal		Q1	Q2	Q3	Q4	ð	Q2	Q3	Q4	D2	D3	D4	RB	RA	GR	ВW	WB	WA	D1	D2	D3	D4	RB	RA	WB	WA	5	GR	GW	D2	D3	D4	RB	RA	WB	WA	5	ЯŖ	GW	D2	D3	D4	RB	RA	WB	WA	D1	GR	GW
	16	20	Vcc	.5 V	-	-	-	-	-	-	-	-	-	=	=	-	=	=	=	-	=	5.5 V	=		-		-	-	-	-	-	=	-		-	-	-	-	-			=	-	-	-	=	=	-		=	-
	15	19		0.7 V 4				2.0 V													-18 mA	5							0.4 V										2.7 V										5.5 V		_
	-																			mA	_								O		_								2									_	2.		_
open).	14		3 WA		-						=								-	-18 mA								0.4 V									_	2.7 V									-	5.5 V			_
≤ 0.7 V; or open)	13		WB		-	-	-	-	-	-	-							4	-18 mA								0.4 V						_				2.7 V										5.5 V				_
	12	15	GW	0.7 V	-	-	-	=	-	-	-							-18 mA													0.4 V									1	2.7 V										5.5 V
2.0 V; low	11	14	GR	0.7 V	-	-	-	-	-	=	=						-18 mA													0.4 V										2.7 V										5.5 V	
Terminal conditions (pins not designated may be high ≥ 2.0 V; low	10	13	Q1	4 mA				-1 mA																																											
may be	ი	12	Q2		4 mA				-1 mA																																										
gnated	8	10	GND	GND	-	-	-	-	-	-	-	-	-	-	=	-	=	-	=	-	=	=	=		=		=	-	-	-	-	=	-		-	-	-	=	-			=	-	-	-	-	=	-		=	-
not desi	2	6	Q3			4 mA				-1 mA																																									_
(pins r	9	ω	Q4				4 mA				-1 mA																																								_
nditions	S	7	RA	0.7 V	-	-	-	-	-	-	-					-18 mA										0.4 V					_					2.7 V										5.5 V					_
ninal co	4		RB		-		-	-	-	=	=				-18 mA	-									0.4 V										2.7 V										5.5 V						_
	e		D4	0			0.7 V				2.0 V			-18 mA	`									0.4 V)									2.7 V										5.5 V	-						_
	2	33	D3			0.7 V				2.0 V			-18 mA	-									0.4 V)									2.7 V										5.5 V								_
	1		D2		0.7 V	0			2.0 V	2		-18 mA	-									0.4 V	0									2.7 V	2									5.5 V	2								_
	ses F					~							0	1	2	3	4	5	ç	7	8		0	1	2	3	4	5	6	7			0	-	2	е С	4	2	9	2			0	1	2	3	4	5	9	7	
			Test no.		2	co.	4			7	8	6	10	11	12	13	1	Ť	Ŧ	Ę	Ĩ		й	2	2	2:	2	5	7	2.			30	en E	č	ά	ė	ñ	Ř	õ	ň	š	4	4	4;	4	4	45	4	4.	4
	MIL-STD-	ol 883 method		3007	-	-	-	3006	-	-	-											3009	-	-	-	-	-	-	-	-	-	3010	-		-	-	-	-	-		-	-	-	-	-	-	-	-	=	=	-
		Symbol		VoL	0			но				<u>0</u>										5								112	113	H								H2	IH3	IH4								IH5	9HI
		Subgroup		-	Tc = 25°C			>				~										_								_	_	_									_	_								_	

TABLE III. Group A inspection for device type 01.

See footnotes at end of device type 01.

		Unit	4	HII	-	-	=	μA	=			=	=	-																							ns		-	-	-	-	=				-	-	
		its	Max	-130	-	-	=	20	=		. 0	07-	-	=																							50		-	45	? =	-	=				50	8 =	
		Limits	Min	-30	-	=	-										2/	-			-	-	-	-	-	-			-		•	-			-		2		-	-	-	-	-				-	-	
		Measured terminal	2	0,00	Q2	Q3	Q4	a1	Q2	03 0	Q4	56	03	Q4																							D1 to Q1	D2 to Q2	D3 10 43	D1 to Q1	D2 to Q2	D3 to Q3	D4 to Q4	RA to Q1	RA to Q2	RA to Q3	RB to Q1	RB to Q2	RB to Q3
	16	20	V _{CC}	> c.c		-	-	-	=			-	-	=			5.0 V	-			-	-	=	-	-	-			-	-	-	-			=		5.0 V		-	-		-	=					-	
	15	19	D1	5.5 V	=	-	=	2.0 V				7.U V					A	-		• •	<u>ء</u>	-	-	-	-	=		. <	< =	-	-	-	m.		-		z			Z	:			GND			5.0 V		
.(r	14	18	AN AN	יין		-	=	0.7 V	=			-	-	-			В	A	8 ×	4 ۵	n =	-	=	-	=	A	ш	۹ ۵	۵ A	с п	A	-	ш	×۵	- د		GND		-	-		-	=					-	
or opei	13	17	MB CRC	-	-	-		0.7 V	-			-	-	=			в	-	A :		<u>ء</u>	-	=	-	-	=	Ā	. a	= נ	A	-	-	е В	. <	(=		GND		-	-			-	= 7			5.0 V		
≤ 0.7 V; or open).	12	15	GW 4 E V		-	-		0.7 V	-			-	=	=			в	-			-	-	=	A	в	=			=		-	A			-		GND		-	-		-	=				-	-	
designated may be high ≥ 2.0 V; low	11	14	GR 4 E V			-		2.0 V (=			-	=	-			В	-				=	=	-	=	=			=	-	-	-			-		GND		-	=		-	-	= :				-	
\wedge	10	13	۵1 ر	GND				2.7 V 2				0.4 V					т	-					=		=	=			=		-	-			-		OUT (+	OUT				OUT			OUT	5	
ay be hi	o	12	Q2 (C	GND				2.7 V		0	0 1 1	>				L	_		_	E -		=	н	-	=			=		-	-			_		_	OUT	+		OUT				OUT		0	OUT	
ated ma	8	10	GND		ڻ -	-	=	-	" 2.			=	5				GND	-				-	=	-	-	=			=		-				-		GND	0		_	0	-	=	= ;	•			0	
design	<u> </u>	6	03 03	פ		GND		_	_	2.7 V			04V		omitted.		ю н								-	-	_						_			-	ი	F		+		OUT		+	ŀ	100			OUT
Terminal conditions (pins not designated may be high	9	8	Q4 0				GND			-	2.7 V		Ċ		C and V _{IC} tests are omitted	and V _{IC} tests are omitted	-			-		-		– н				-	-							Č.		č	B	_			Τ	+	č		5		
litions (ç				7 V			2.1			0.4 V	C and V _{IC}	and V _{IC} te	B			-	- L		-			-	- 		-	-	-	-	~		-	I T _C = -55°C.	ą		L C	5 	-		.no	_		ΞC	5 G	2	TIC
al conc	u)	-	RA RA		-	-		o.	-	-		-	-	-	c = +125°(c = -55°C			_					- m		A		< □					_	< □	א נ	125°C and	D		-	-	-	-	-	_			ß	5	
Termir	4	2	T RB	+	-	-		0.7 V	-		-	-	-	-	except T	except T	В		A -		= د	<	τ =	В	-	-	A	: a] =	A	-		Ω.	- <	. =	$= pt T_c = +$	С О		-	-	-	-	-			· ·	<u>≥</u>	-	
	n	4	3 D4	+		_	5.5 V			-	2.0 V	+	>	2.0 V	ubgroup 1,	ubgroup 1,	В				≮ =	=	=	-	-	=		-	=	-	-		<u>е</u>	-	-	oup 7 exc		╉	2	╞	╞		∠	+		NU C	ō		د ۲
	0	33	D3	+	>	5.5 V				2.0 V	+	-	201		imits as su	mits as su	A	-	•		= ۵	=	=	-	=	=		: <	=	-	-	-	Ω,	•	-	for subgru		4	Í	╞	╞	Z		+	0	2 C		>	5.0
	-	0	o. D2	t. 1	5.5 V				2.0 V		+	100	7.0		ons, and li	ons, and li	В	-	•		≮ =	=	=	-	-	=		: =	=	-	-	-	Ω.	-	-	ditions as		Z	+	╞	Z				GNI			5.0	
	Cases E, F	Case 2	Test no.	50	51	52	53	54	55	56	27	202	60	61	nal conditic	nal conditic	62	63	64	65	00	10	00	20	71	72	73	75	92	22	78	29	80	81 81	83	minal con	84	85	00 87	88	89	06	91	92	93	94 05	96 96	97	98 00
	MIL-STD-	883 method	2006	3011	-	-	-								Same tests, terminal conditions, and limits as subgroup 1, except $T_{\rm C}$ = +125°	ests, termir	3014				-	-	-	-	-	-			-	-	-	-			-	sts and ter	3003	Fig. 4	-	=	-	-	-				=	-	
		Symbol	-	100 2/				НZО				OZL			Same te		Truth		tests						_				_							Same te	tPLH1			1 1	С.			PLH2	7			- L	
		Subgroup	•	Tr = 25°C				_			_	_			2	3	7 <u>3/4</u> /	Tc = 25°C																		8	б	Tc = 25°C		+-	<u>, </u>			t	7			9	

TABLE III. Group A inspection for device type 01.

See footnotes at end of device type 01.

		Unit		ns	-	=	-	=	-	-	=	=	=		=	=	-	=	=	-	-		=		=	=	-	-	-	-	=	-	-	=	-	-	=	
		its	Max	50	-	-	-	55	-	=			=	=	=	40	-	-	=	-	=		=	45	=	=	=	65	58	58	65	65	72	72	52	52	58	
		Limits	Min	2	-			=	-	-			-	-	=	=	-		=	-	-		=		-	=	-	-	-		-	=			=	-		
		Measured terminal		GW to Q1	GW to Q2	GW to Q3	GW to Q4	GW to Q1	GW to Q2	GW to Q3	GW to Q4	GR to Q1	GR to Q2	GR to Q3	GR to Q4	GR to Q1	GR to Q2	GR to Q3	GR to Q4	GR to Q1	GR to Q2	GR to Q3	GR to Q4	GR to Q1	GR to Q2	GR to Q3	GR to Q4											
	16	20	V _{cc}	5.0 V	-	-	-	-	-	-				=	=	=	-	-	=	-	-		=			=	=											
	15	19	D1	5.0 V				GND				5.0 V				5.0 V				GND				GND														
<i>.</i>	14	18	WA	N	-		-	-	-	-		GND			=	=	-		=	-	=		=			=	-											
or oper	13	17	WB	GND	-		-	-	-	-			-	-	-	=	-		-	-	-		=		-	-	-											
/\ \. \ ^ . \	12	15	/	N	-		-	=	-	-		GND			=		-			-	-		=				=											
∠.U V; IOW ≤ U. / V; OI OPEN)	11	14		GND	-			=	-	-		N	=	=	=	=	-		=	-	=		=		=	=	=		_									
<u>∪. ∠ > n(</u>	10							Т								Т				Т				Τ					as for subgroup 9, except $T_c = +125^{\circ}C$ and test limits as shown									
y be nic		13		OUT	-			DUD	T			OUT	Т			OUT	F			OUT	Т			OUT	Т				test limits									
IEN IIIA	თ	12	D Q2		OUT				OUT				OUT				OUT				OUT				OUT				25°C and									
I erminal conditions (pins not designated may be high \ge	ø	10		GND	-	- L	-	-	=	-		-	=	г -	-	=	=	- L	=	=	-	- L	=	-		Γ "	-		ot $T_c = +1$									
	2	ი	Q3			OUT				OUT				OUT				OUT				OUT				OUT			p 9, excel									
ions (pi	9	œ	Q4	/			OUT				OUT				OUT				OUT				OUT				OUT		or subgrou									~
II CONUUL	2	7	RA		-	-	-	-	-	-	-	GND	-	-	-	=	-	-	-		-	-	=	"	-	-	=		tions as fc									Γ _C = -55°C.
ellille	4	ى ك	RB	GND	-	=	-	=	-	-		=	-	-	-	=	-	=	=	-	-		=	=	-	=	=		Same tests and terminal conditions), except ⁻
	ო	4	D4				5.0 V				GND				5.0 V				5.0 V				GND				GND		and term									bgroup 1(
	2	m	D3			5.0 V				GND				5.0 V				5.0 V				GND				GND			ame tests									as for su
	-	5	D2		5.0 V				GND				5.0 V				5.0 V				GND				GND				й									and limits
	Cases E, F	Case 2	Test no.	100	101	102	103	104	105	106	107	108	109	110	111	112	113	114	115	116	117	118	119	120	121	122	123	124	125	126	127	128	129	130	131	132	133	conditions
	MIL-STD-	883 method		3003	Fig. 4		-	-		-	-	-	-	-	-	-	-		=	-	-	-	-	=	-	=	-	-	-	-		-		-	-	-		Same tests, terminal conditions and limits as for subgroup 10, except $T_{\rm C}$ = \cdot
	~	Symbol		t _{PLH3}	/9			PHL3	-	1		DHZ				РZH				PLZ				PZL				t _{PLH1}	t _{PHL1}	PLH2	PHL2	PLH3	PHL3	DHZ	РZH	PLZ	PZL	Same test
		Subgroup		6	Tc = 25°C			t.	7			t				t				t				t				10	T _C =125°C	t.	t.	t	t.	t	t	t	t	11

TABLE III. Group A inspection for device type 01.

 $\underline{1}/$ Min/max limits (µA) for circuits, unless otherwise specified.

	E	-120/-360 except -135/-370 except	0.5/-360 for test 22 -150/-380 for test 23;	-135/-380 for tests 24, 25, 26	36 mA/-1.08 mA48 mA/-1.20 mA	-240/-720 -320/-800
Min/max limits (mA)	U	-160/-400 except -120/-	-120/-360 for test 24 -0.5/-36		-305/-76036 m	-305/-760 -2
	B	-30/-300			006-/06-	-60/-600
	A	-120/-360			-36 mA/-1.08 mA	-240/-720
	Test	lıL1			1112	l _{IL3}

 $\frac{2}{4}$ l_{os} limits for circuits B, C, and E are -15/-100 mA. $\frac{3}{4}$ Connect a 0.5 kΩ to 2 kΩ resistor from terminals, 6, 7, 9, and 10 to V_{cc} for subgroup 7 tests. $\frac{4}{4}$ A = 3.0 V min., B = 0.0 V or GND, C = pulse 3.0 V - 3.0 V

 $\overline{5}/$ Output voltages shall be: H > 1.5 V, L < 1.5 V $\overline{6}/$ Load ground into register under test prior to test. $\overline{7}/$ Load one state into register under test prior to test.

		Unit		>	-	-		μA	-	-	-	>	-	-	-	-			-	=		μA		-	-	-						-								-	=	=	=	-	-		-	-	=	-
		ts	Мах	0.4	-	-	-	20	-	=	-	-1.5	-	-	=	=	-	-	-	-	-	1/	-	-	-	-					:	20		-					. 0	9	0 ¹ 01	8=	-	=	=	-	=	-	200	200
		Limits	Min																			1/																						Ī						
		Measured terminal		a1	Q2	Q3	Q4	a1	Q2	Q3	Q4	D2	D3	D4	RB	RA	GR	GW	WB	WA	D1	D2	D3	D4	RB	RA	WB	WA A		2 CK	٩ و	D2	ß	4	л Ц	KA	WB	WA	50		56	22	24	50	0 7 0 7 0	S AW	WA	D1	GR	GW
		20	V _{cc}	4.5 V	-		-	=	=		-	-		-	-		-	=	-	=	-	5.5 V	-	-	-	-						-								-	-	-	-	-	=	-	-	-	=	-
	15	19		0.7 V				2.0 V													-18 mA								0.4 V						Ī	Ī			Z./ V					t				5.5 V		
	14	18	WA	0.7 V	-	-	-		=	=	-									-18 mA								0.4 V										2.7 V						-			5.5 V			
or open	13	17		0.7 V 0	-		-		=		-								-18 mA	-1							0.4 V									;	2.1 V				-		+			55 \	+		-	
≤ 0.7 V; or open)	12			0.7 V 0.	_	_	-	_	-	_	_			_	_			-18 mA	-								0				0.4 V		+	+		•	N			7 1/	>	$\left \right $	+	+		Ľ	2		╞	5.5 V
2.0 V; Iow ≤					-	-		-	-	-	-							-18									_			-	0.4			_					~	_	i		+	_					-	
Λ	11	14	GR	0.7 V	-	-		-	=	-	-						-18 mA				_		_							0.4 V				_					~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	7.7	+		-	_					5.5 V	_
be high	10	13	ð	4 mA				5.5 V																																	_									
Ε	6	12	Q2		4 mA				5.5 V																																_		_	_					Ļ	
not designated	8	10	GND	GND	-	-	-	-	=	-	-	-	-	=	=		-	-	-	-	-	-	-	-	-	-						-		-		•				-	-	-	-	-	-	-	-	-	=	-
p	2	6	Q3			4 mA				5.5 V																																								
ns (pins nc	9	æ	Q4				4 mA				5.5 V																																							
conditio	5	7	RA	0.7 V	-	-	-	=	=	=	-					-18 mA										0.4 V										2.7 V									551	> 0.0				
Terminal conditions (pins	4	5	RB	0.7 V	-		-		=		-				-18 mA										0.4 V									111	Z. / V									E E V	0.0 4					
	3	4	D4				0.7 V				2.0 V			-18 mA										0.4 V									11 4 0	2.1 V									55V	> > >						
	2	ю	D3			0.7 V				2.0 V			-18 mA										0.4 V										2.7 V									5 5 /	× 0.0							
	٢	2	D2		0.7 V				2.0 V			-18 mA										0.4 V										2.7 V									55V	> 0.0								
	Cases E, F	Case 2	Test no.	-	2	e	4		9	7	œ	6	10	11	12	13	14	15	16	17			20	21	22	23	24	25	97	27			30	0	32	33	34	35	36	38		t	41	-+	42	44	45	46	47	48
	MIL-STD-	883 method		3007	-	-	-		1	<u> </u>	I			1	1							3009	-	-	-	-				-		3010		-						=	=	-	-	-	=	-	-	-	-	-
	M	Symbol		NoL				CEX				ō										5							+	112	-									H2	Ê I	H4							H5	H6
		Subgroup			$Tc = 25^{\circ}C$,										_																												

TABLE III. Group A inspection for device type 02.

See footnotes at end of device type 02.

	Unit		шA																									ns _				-	-			=	-			=			-
	ts	Мах	40																									20			-	40	-	-	-	45		-	-				-
	Limits	Min				4/	-	-	-	-	-	-	-	-	-	=	-	-	=	=	-	-	-	=	-	-		2			-	-	-	-	-	=		-	-	-			
	Measured terminal	I	V _{cc}																									D1 to Q1	D2 to Q2	D3 to Q3	D4 to Q4	D1 to Q1	D2 to Q2	D3 to Q3	D4 to Q4	RA to Q1	RA to Q2	RA to Q3	RA to Q4	RB to Q1	RB to Q2	RB to Q3	RB to Q4
16	20	V _{cc}	5.5 V			5.0 V	-				=	-	-	=	=	=	-	=	=	=	=	-	=	-	-	-		5.0 V		-	-	= :	-	-	-	-		-	-	=			
15	19	D1	4.5 V			A	-		=	В	=	=	-	=	=	=	=	=	A	=	=	=	В	=	=	=		Z				Z				5.0 V				5.0 V			
14	18	WA	GND			в	A	В	A	В		=	-	=	=	A	ш	A	в	A	в	A	в	A	ю	-		GND				-	-	=	=			-		GND		= :	-
13 00	17	WB	GND			в	-	A	-	В	-	-	-	A	в	=	A	=	в	=	A	-	В	-	A	-		GND		-	-	-	-	-	-	-	-		-	5.0 V	- 1		-
11 12 13 13 1	15		4.5 V			в	-	-	-	-	-	=	A	-	в	-	=	-	-	-	-	-	A	-	-	=		GND		-		=	-	-	-		-		-	-	=	-	-
11	14	GR				в	-	-	-			=	=	=	A	в	=	=	A	-	-		В	-	-	=		GND			-	-	-	-	-	-	-				-		-
d	13	б а	4			т	-	-	-	L	н	=	-	_	т	_	-	=	т	=	=		=	-	=	=		OUT (OUT				OUT				OUT			_
8 0 0 0	12	Q2 (н	L	_	-	Т	=	=	=	=	=	-	=			=	=	=		_	OUL			_	OUT			0	OUT				OUT		_
8	10	GND 0	Q			GND	-	-	-			-	-	-	-	=	=	=	-	=	-			-	-	-	·	GND	с		_	-	o ₌	-	-	-	•				0		-
	6	Q3 G	U	omitted.	nitted.	Ю	-			1	н	_	-		н	_	-	-	н	-	=			-	=	-	·	U		OUT				OUT				OUT				OUT	_
9	80	Q4 C		tests are i	ests are or	_				H	-			- т	-										-	-	č.				5			_	OUT			ō	OUT				OUT
			Q	C and V _{IC}	and V _{IC} te	В	A	В	· ·	B		Ē	_		-	_	Ē	_	Ē	_	В	۲. ح	В		ш	_	$1 T_{c} = -55^{\circ}$	QN.			no			_		z		-		DN		Ì	วี
4 5	2	B RA		c = +125°(c = -55°C	е В	+		A						-	A						1		A		A	125°C and	U				-	-	-	-	~	-	-	-	G	-	-	
	5	BB t		except T	except T	В	-	A	=	В		A		B	-	=	A	-	B	-	A	-	В	-	A	-	$pt T_c = +$	GND		-	-	-	-	-	-	-	=	-	" ^	Z	-	-	: >
e	4	В		bgroup 1	ubgroup 1	В	-	-	-	A		-	ш	-	-	A	-	=	-	=	-	-	В	-	-	-	oup 7 exce				Z				Z			۸	5.0 V			-	5.0 V
2	e	ß		imits as su	imits as su	A	-	-	-	В	-	-	-	-	-	=	-	=	A	-	-	-	В	-	-	-	for subgre			Z				Z				5.0 V				5.0 V	_
-	7	o. D2		ons, and li	ons, and li	B	-	=	=	A	-	-	-	-	-	=	=	=	-	=	-	-	В	-	-	-	ditions as		Z				Z				5.0 V				5.0 V		_
Cases		Test no	49	nal conditic	nal conditic	50	51	52	53	54	55	56	57	58	59	09	61	62	63	64	65	99	67	68	69	20	rminal con	71	72	73	74	75	76	22	78	79	80	81	82	83	84	85	86
MIL-STD-			300£	Same tests, terminal conditions, and limits as subgroup 1, except $T_c = +125^{\circ}C$ and V_{1c} tests are omitted.	ssts, termin	3014	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	=	Same tests and terminal conditions as for subgroup 7 except $T_c = +125$ °C and $T_c = -55$ °C	3003	Fig. 4		-	-	-	-	-	-	-	-	-	=			-
	Symbol		loc					tests																			Same te	t _{PLH1}				PHL1				PLH2	1			PHL2	7		
	Subgroup		1 Tc = 25°C	2	e	7 2/3/	$Tc = 25^{\circ}C$																					თ	Tc = 25°C			t				t	5			t	5		

TABLE III. Group A inspection for device type 02.

See footnotes at end of device type 02.

		Unit		ns	-		-	-	-	-				=	-		-		-	-	-	-	-	-	=	-	=	
		its	Мах	50	=	=		45	=	=	-	40	=	-	=	-	=	=		65	52	58	58	65	58	46	46	
		Limits	Min	2	-	-		=	-	-	-	-	-	=		-	-	-		-	-	-		-		-		
		Measured terminal	•	GW to Q1	GW to Q2	GW to Q3	GW to Q4	GW to Q1	GW to Q2	GW to Q3	GW to Q4	GR to Q1	GR to Q2	GR to Q3	GR to Q4	GR to Q1	GR to Q2	GR to Q3	GR to Q4									
	16	20	V _{cc}	5.0 V	-			=	-					=														
	15	19	D1	5.0 V				GND				GND				GND												
en).	14	18	WA	N	=			=	=		-	GND		=			=											
'; or ope	13	17	WB	GND	=	=		=	=	=	=	-	=	-	=	-	=	=										
v ≤ 0.7 \	12	15	GW	N	-	=		-	-	=		GND	=	=		-	=	=										
.0 V; lov	11	14	GR	GND	=				=	=	-	N	=	=	=						MN							
Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.7 V; or open)	10	13	ð	OUT				OUT				OUT				OUT					as for subgroup 9, except $T_{\rm C}$ = +125°C and test limits as shown							
may be	თ	12	Q2		OUT				OUT				OUT				OUT				and test li							
gnated	ω	10	GND	GND	-	=		=	-	=	-	-	=	-	=	-	=	=			= +125°C							
not desi	7	თ	Q3			OUT				OUT				OUT				OUT			except T _c							
s (pins 1	ø	ω	Q4				OUT				OUT				OUT				OUT		ogroup 9,							
Indition	ω	2	RA	5.0 V	-	=		=	=	=	=	GND	=	-	=	"	=	=			as for sub							-55°C.
minal cc	4	ى ک	RB	GND	-			=	-		-	-		-		-					conditions							cept T _c =
Terr	m	4	D4		-		5.0 V		-		GND				GND				GND		d terminal							oup 10, ex
	5	ю	D3			5.0 V				GND				GND				GND			Same tests and terminal conditions							for subgr
	-	5	D2		5.0 V			_	GND				GND				GND				Sam							nd limits as
	Cases E, F	Case 2	Test no.	87	88	89	06	91		93	94	95		97	98	66	100	101	102	103	104	105	106	107	108	109	110	Same tests, terminal conditions and limits as for subgroup 10, except T_{C} = -55°C.
	MIL-STD-	883 method	1	3003	Fig. 4	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	=	ts, terminal
				t _{PLH3}	5/			5HL3	~			PLH4				PHL4				tpuh1	t _{PHL1}	PLH2	PHL2	5HU4	PHL3	PLH4	PHL4	Same tes
		Subgroup Symbol		6	$Tc = 25^{\circ}C$			t	6			t				t				10	T _c =125°C	t	t	t	t	t	t	11

<u>1</u>/ Min/max limits (μA) for circuits, unless otherwise specified.

	F	-135/-370 except	-150/-380 for test 23		-320/-800	-320/-800
its (mA)	Е	-120/-360 except	-0.5/-360 for tests	22 and 24	-240/-720	-240/-720
Min/max limits (mA)	С	-160/-400 except	-120/-360 for test 24		-305/-760	-305/-760
	В	-30/-300			006-/06-	-60/-600
	A	-120/-360			-240/-720	-240/-720
	Test	l _{IL1}				lı.3

2/ Connect a 0.5 kΩ to 2 kΩ resistor from terminals, 6, 7, 9, and 10 to V $_{
m CC}$ for subgroup 7 tests.

3/ A = 3.0 V min., B = 0.0 V or GND, C = pulse 3.0 V - - - - 3.0 V 0.0 V

 $\underline{4}$ Output voltages shall be: H > 1.5 V, L < 1.5 V

 $\overline{5}$ / Load ground into register under test prior to test.

 $\underline{6}$ / Load one state into register under test prior to test.

TABLE III. Group A inspection for device type 02.

5. PACKAGING

5.1 <u>Packaging requirements.</u> For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department of Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature which may be helpful, but is not mandatory.)

6.1 <u>Intended use.</u> Microcircuits conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

- 6.2 Acquisition requirements. Acquisition documents should specify the following:
 - a. Title, number, and date of the specification.
 - b. Complete part number (see 1.2).
 - c. Requirements for delivery of one copy of the quality conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
 - d. Requirements for certificate of compliance, if applicable.
 - e. Requirements for notification of change of product or process to contracting activity in addition to notification to the qualifying activity, if applicable.
 - f. Requirements for failure analysis (including required test condition of method 5003 of MIL-STD-883), corrective action, and reporting of results, if applicable.
 - g. Requirements for product assurance options.
 - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
 - j. Requirements for "JAN" marking.

6.3 <u>Superseding information</u>. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.

6.4 <u>Qualification</u>. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43123-1199.

6.5 <u>Abbreviations, symbols, and definitions.</u> The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and as follows:

GND	Current flowing into an input terminal. Input clamp voltage. Voltage level at an input terminal. Output current in the high impedance mode with the output voltage low. Output current in the high impedance mode with the output voltage high.
чни	reference points on the input and output voltage waveforms with the three state output changing from the defined high level to a high impedance (off) state. Output disable time from low level - The time between the specified reference points on the input and output voltage waveforms with the three state output changing from the defined low level to a high impedance (off) state.
tрzн	Output enable time to high level - The time between the specified reference points on the input and output voltage waveforms with the three state output changing from a high impedance (off) state to the defined high level.
t _{PZL}	Output enable time to low level - The time between the specified reference points on the input and output voltage waveforms with the three state output changing from a high impedance (off) state to the defined low level.

6.6 <u>Logistic support.</u> Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired for Government logistic support will be acquired to device class B (see 1.2.2), lead material and finish A (see 3.4). Longer length leads and lead forming should not affect the part number.

6.7 <u>Substitutability.</u> The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-38510 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-PRF-38535.

Military device type	Generic-industry type
01	54LS670
02	54LS170

6.8 <u>Manufacturers' designation</u>. Manufacturers' circuits, which form a part of this specification, are designated with an "X" as shown in table IV herein.

	Manufacturer					
	Circuit A	Circuit B	Circuit C	Circuit E	Circuit F	
Device type	Texas Instruments	Signetics Corp.	National Semiconductor	Fairchild Semiconductor	Motorola Inc.	
01	Х	Х	Х	Х	Х	
02	Х	X	X	Х	Х	

TABLE IV. Manufacturer's designator.

6.9 <u>Changes from previous issue</u>. Asterisks are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

Custodians: Army - CR Navy - EC Air Force - 11 DLA - CC Preparing activity: DLA - CC

(Project 5962-1966)

Review activities: Army - MI, SM Navy - AS, CG, MC, SH, TD Air Force - 03, 19, 99

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL							
INSTRUCTIONS 1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.							
2. The submitter of this form must complete blocks 4, 5, 6, and 7, and send to preparing activity.							
3. The preparing activity must provide a reply within 30 days from receipt of the form.							
NOTE: This form may not be used to request copies of documents, nor to request waivers, or clarification of requirements on current contracts. Comments submitted on this form do not constitute or imply authorization to waive any portion of the referenced document(s) or to amend contractual requirements.							
I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-M-38510/319C	2. DOCUMENT DATE (YYYYMMDD) 2003-07-14					
3. DOCUMENT TITLE MICROCIRCUITS, DIGITAL, LOW-POW	ER SCHOTTKY TTL, 4 BY 4 REG	GISTER FILE, CASCADABLE, MONOLITHIC	SILICON				
4. NATURE OF CHANGE (Identify paragraph	number and include proposed rewrite,	if possible. Attach extra sheets as needed.)					
5. REASON FOR RECOMMENDATION							
6. SUBMITTER							
a. NAME (Last, First Middle Initial)	b. ORGANIZAT	ΠΟΝ					
c. ADDRESS (Include Zip Code)	d. TELEPHONE (1) Commercial (2) DSN (If applicable						
8. PREPARING ACTIVITY		E (Include Area Code					
a. NAME Defense Supply Center, Columbus		E (Include Area Code I 614-692-0536 (2) DSN 850-0536					
c. ADDRESS (Include Zip Code) DSCC-VA P. O. Box 3990 Columbus, Ohio 43216-5000	Defense Star 8725 John J. Fort Belvoir, ^N	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Standardization Program Office (DLSC-LM) 8725 John J. Kingman Road, Suite 2533 Fort Belvoir, Virginia 22060-6221 Telephone (703)767-6888 DSN 427-6888					
DD Form 1426, FEB 1999 (EG)	PREVIOUS EDITIONS ARE OF	BSOLETE. WHS/DIOR, F	Feb 99				